List of Figures

Figure 1.1: A coffee cup and dough-nut have the same topological invariant. 2

Figure1.2: Topological change from a topological insulator to an ordinary insulator. 6

Figure1.3: Typical geometry of the Hall Effect. Current (I_x) flows in plane, perpendicular to an applied field B inducing a mutually orthogonal potential V_x by action of the Lorentz force. 7

Figure1.4: Transverse and longitudinal components or resistivity revealing the quantum Hall Effect for a GaAs-$Ga_{0:71}Al_{0:29}$ as heterostructure. ρ^{xy} shows quantization in units of h/ne^2 where n is an integer. 8

Figure 1.5: Diagrammatic picture of the electron localization into cyclotron orbitals leading to edge states. 10

Figure 1.6: Left: QHE with both right-moving and left-moving edge states. These states are robust to scattering by impurities. Right QSHE with upper state right moving spin up and left-moving spin down. The lower state is inverted by comparison. Back-scattering is suppressed from non-magnetic impurities. 12

Figure 1.7: Diagrammatic depiction of the two different scattering paths around an impurity for the quantum spin Hall state. The total path difference between them is 2π, leading to total suppression of the back scattering for Fermions. 13

Figure1.8: Helical edge states in the 2D TI. 15

Figure1.9: Band structure of CdTe/HgTe quantum well. Band inversion occurs when the well thickness is larger than the critical thickness. 16

Figure1.10: Experimental verification of TI behavior in CdTe/HgTe quantum well. The precise quantization of the current is confirmed by a conductance value of $2e^2/h$. 17

Figure1.11: The surface band dispersion second-derivative image of $Bi_{0.9}Sb_{0.1}$ along along ***Γ***-***M***. There are a total of 5 crossings between ***Γ*** and ***M*** which indicates topologically non-trivial surface states. 18

Figure1.12:High resolution ARPES measurement of the surface electronic band dispersion on Bi_2Se_3 demonstrating the Dirac cone formed by the TSS. 19

Figure1.13: Characterization of MBE grown Bi_2Se_3 showing thickness independent behavior. 21

Figure1.14: Transport characterization of $Bi_2(Se_xTe_{1-x})_3$ nanowires indicating strong weak anti-localization. 21

Figure1.15: Bulk insulating behavior if BSTS by Ando group. 22

Figure 1.16: Spin texture in TI in k-space showing the spin momentum locking of the surface states. 23

Figure1.17: Device structure used for detecting spin momentum locking in TI. The use of a FM voltage detector enables detection of the current induced spin polarization of the TSS. 24

Figure1.18: Voltage signal demonstrating the current induced spin polarization in TI. Obvious hysteresis is observed when the magnetic field is perpendicular to the current direction. The hysteresis signal is reversed on reversing the current direction. No hysteresis signal is observed when the external field is parallel to the current direction. 25

Figure1.19: The device structure and measurement geometry for TI channel with FM detector demonstrating the signal corresponding to the current induced spin polarization of the TSS. 26

Figure1.20: Current induced magnetization switching in $(Bi_{0.5}Sb_{0.5})_2Te_3/(Cr_{0.08}Bi_{0.54}Sb_{0.38})_2Te_3$ heterostructure at constant in-plane external field of 0.6 T and -0.6 T. 28

Figure1.21: (a), (b) Band structure calculations of Bi_2Se_3 and Bi_2Te_3 respectively, showing the Dirac point crossing at 0 momentum. (c) ARPES of Bi_2Se_3 showing Dirac point in the band dispersion. (d) ARPES of Bi_2Te_3 similarly showing the Dirac band dispersion. 29

Figure1.22: Bi_2Se_3 doped with varying levels of Fe in the bulk of the film. A gap opening at the gamma-point is seen as a function of doping. 30

Figure 2.1: (a) Mechanism and (b) experimental set up of XRD instrument (Rigaku Mini Flex II). 32

Figure 2.2: Schematic diagram of test circuit for measuring resistivity with the four-point probe method. 34

Figure 2.3: Schematic diagram for Hall Effect measurement. 35

Figure 2.4: Schematic diagram for thermoelectric measurement. 36

Figure 2.6: (a) 2ω detection principle. (b) SQUID detection schematic. (c) MPMS instrument set up used for characterization. 38

Figure 2.7: Schematic diagram of SQUID magnet. 39

Figure 3.1. The X-ray diffraction patterns of $(Bi_{1-x}Co_x)_2Se_3$ (with x=0, 0.04, 0.05, 0.06). 43

Figure 3.2. a) Temperature variation of resistivity of $(Bi_{1-x}Co_x)_2Se_3$ (with x=0, 0.04, 0.05, 0.06). Inset: The variation of band gap (which opens due to application of magnetic field) with external magnetic field of $(Bi_{0.94}Co_{0.06})_2Se_3$. (b) Temperature variation of Seebeck Coefficient of $(Bi_{1-x}Co_x)_2Se_3$ (with x=0, 0.04, 0.05, 0.06). Inset: The variation of power factor with temperature of $(Bi_{1-x}Co_x)_2Se_3$. 44

Figure 3.3: Magnetic field variation of magneto resistance ratio of $(Bi_{1-x}Co_x)_2Se_3$ [with x=0 (a), 0.04 (b), 0.06 (c)] at different temperature. (d) Temperature variation of *a* and *b* parameters of $(Bi_{1-x}Co_x)_2Se_3$. We have shown the parameters for undoped and maximum doped samples. 46

Figure 3.4: Temperature variation of Hall resistivity of $(Bi_{1-x}Co_x)_2Se_3$ [with x=0 (a), 0.04 (b), 0.06 (c)]. (d) Magnetic hysteresis loops of $(Bi_{1-x}Co_x)_2Se_3$ (with x=0, 0.04, 0.05, 0.06). Inset: The close-up view of M(H) curve to show the hysteresis loop. 49

Figure 4.1: Hall resistivity as a function of magnetic field for $Bi_2Se_{3-y}S_y$. Insets: Temperature variations of carrier concentration and Hall mobility. 54

Figure 4.2: (a) Resistivity as function of temperature of$Bi_2Se_{3-y}S_y$. (b) Total DOS of S doped Bi_2Se_3. Vertical line marks the Fermi energy. 55

Figure 4.3: MR of $Bi_2Se_{3-y}S_y$ as function of magnetic field at different temperatures. We have not shown here the resistivity of y=0.15 sample which shows consistent and similar behavior. 56

Figure 4.4: SdH oscillation and Landau level index of$Bi_2Se_{3-y}S_y$ (with y=0, 0.06, 0.21, 0.30) shown from $-d^2\rho_{xx}/dB^2$ as function of inverse magnetic field. Insets: Fast Fourier transform of the SdH oscillations. 57

Figure 4.5: (a) Fitting of conductivity as function of magnetic field of $Bi_2Se_{3-y}S_y$ with HLN model. (b) Channel density of $Bi_2Se_{3-y}S_y$ as a function of temperature estimated from HLN model fitting. 61

Figure 5.1: Magnetic field variation of Magneto-resistance at different temperatures of Bi_2Se_3, BiFeS-L, BiFeS-M and BiFeS-H. Inset: Temperature variation of resistivity at different magnetic fields. 65

Figure 5.2: Magnetic field variation of magnetization of Bi_2Se_3, BiFeS-L, BiFeS-M and BiFeS-H at different temperatures. 68

Figure 5.3: (a), (b) and (c) shows the ARPES spectra of BiFeS-L, BiFeS-M and BiFeS-H respectively collected by photons of energy 21.2 eV. (d) and (e) shows the second derivative of ARPES images for BiFeS-L and BiFeS-H respectively. The green dots in (d) depicts the Dirac cone structure. (f) shows the comparison of the EDC's at the Γ-point of the Brillouin zone for all the samples. 69

Figure 5.4: Landau level index (obtained from MR quantum oscillations) as a function of inverse magnetic field of Bi_2Se_3, BiFeS-L, BiFeS-M and BiFeS-H. Inset (right): Quantum oscillation obtained from magnetic field dependence MR data. Inset (left): First Fourier transform of quantum oscillations. 72